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Docket No. 740756-2064
12203

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

in re Patent application of:)
Shunpei YAMAZAKI et al.)
Serial No.: 09/437,135) Group Art Unit: 2813
Filed: November 10, 1999) Examiner: E. Kielin
For: SEMICONDUCTOR DEVICE AND)
METHOD FOR FORMING THE SAME)

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AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

Responsive to the Office Action dated **August 14, 2002**, the following amendments and remarks are submitted in connection with the above-identified application.

IN THE CLAIMS:

Please amend claims 1, 6, 11, 30 and 34 as follows. Attached hereto is a marked up copy of the claims in their amended form.

Sub F 1. (Four Times Amended) A method for manufacturing a thin film transistor comprising the steps of:

forming a semiconductor film comprising amorphous silicon over a substrate;

crystallizing said semiconductor film by irradiating a laser light;

patterning the crystallized semiconductor film to form first and second semiconductor islands;

forming an insulating film comprising silicon oxide on each of said first and second semiconductor islands by a vapor phase deposition using TEOS at a temperature of 200 to 400° C.;